

LISTING OF THE CLAIMS:

Claims 1-10 (Cancelled)

11. (Currently Amended) A Fin structure comprising:

a structure having at least one vertically oriented semiconductor body present thereon, wherein said at least one vertically oriented semiconductor body has vertical surfaces;

a doped region, comprised of a concentration of dopant ions, present in said at least one vertically oriented semiconductor body that extends inward from said vertical surfaces, wherein said dopant ions are diffused into said semiconductor body to a predetermined depth that is dependent on the thickness of the semiconductor body and the concentration of the dopant ions; and

contacts present on outer portions of said at least one vertically oriented semiconductor body, wherein said doping region and said contacts are of the same dopant type thereby providing a resistor in said at least one vertically oriented semiconductor body.

12. (Original) The Fin structure of Claim 11 wherein said at least one vertically oriented semiconductor body is comprised of single crystalline Si or SiGe.

13. (Original) The Fin structure of Claim 11 wherein said at least one vertically oriented semiconductor body has a hard mask present atop a horizontal surface.

14. (Original) The Fin structure of Claim 11 wherein said at least one vertically oriented semiconductor body has a patterned masking layer thereon, said patterned masking layer not covering said contacts.

15. (Original) The Fin structure of Claim 14 wherein said patterned masking layer is comprised of a conductive material.

16. (Original) The Fin structure of Claim 15 wherein said patterned masking layer is comprised of a non-conductive material.

17. (Cancelled).

18. (Currently Amended) The Fin structure of Claim ~~17~~ 20 wherein said diode includes said contacts that are of opposite dopant style.

19. (Currently Amended) The Fin structure of Claim ~~17~~ 20 where said diode includes said contacts wherein one of the contacts comprises a doped region having a conductivity type dopant which is different from said dopant region and the other contact is a silicide.

20. (New) A Fin structure comprising:

a structure having at least one vertically oriented semiconductor body present thereon,
wherein said at least one vertically oriented semiconductor body has vertical surfaces;

a doped region, comprised of a concentration of dopant ions, present in said at least one vertically oriented semiconductor body that extends inward from said vertical surfaces, wherein said dopant ions are diffused into said semiconductor body to a predetermined depth that is dependent on the thickness of the semiconductor body and the concentration of the dopant ions; and

contacts present on outer portions of said at least one vertically oriented semiconductor body, wherein said doping region and one of said contacts are of opposite dopant type thereby providing a diode in said at least one vertically oriented semiconductor body.

21. (New) A Fin structure according to Claim 11, wherein said contacts comprise further doped regions formed in upper, horizontal surfaces of the semiconductor body and laterally extending thereacross.

22. (New) A Fin structure according to Claim 11, wherein:

said doped region includes:

- i) a first doped portion of the semiconductor body extending inward from a first vertical surface of the semiconductor body; and
 - ii) a second doped portion of the semiconductor body extending inward from a second vertical surface of the semiconductor body;
- and

the semiconductor body includes an undoped portion laterally extending between and separating said first and second doped portion.